



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



DATA SHEET

BTA212X series B
Three quadrant triacs
high commutation

Product specification

September 1997



Three quadrant triacs high commutation

BTA212X series B

GENERAL DESCRIPTION

Glass passivated high commutation triacs in a full pack, plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commute the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

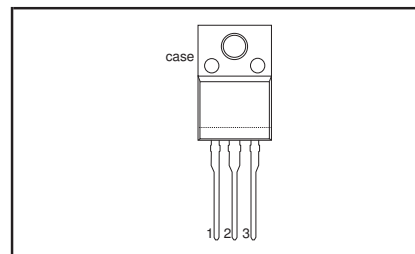
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages	500B	600B	800B	V
		500	600	800	
		12	12	12	
$I_{T(RMS)}$	RMS on-state current	12	12	12	A
I_{TSM}	Non-repetitive peak on-state current	95	95	95	A

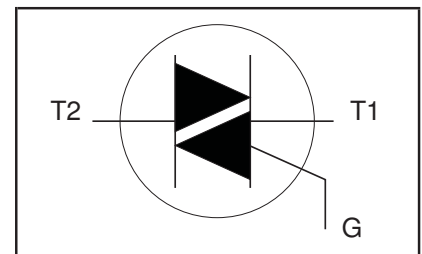
PINNING - SOT186A

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500 500 ¹	-600 600 ¹	-800 800	
V_{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	-800 800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{hs} \leq 56^\circ\text{C}$	-	12			A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25^\circ\text{C}$ prior to surge	-	95			A
I^2t	I^2t for fusing	$t = 20\text{ ms}$	-	105			A
dI_T/dt	Repetitive rate of rise of on-state current after triggering	$t = 16.7\text{ ms}$	-	45			A^2s
I_{GM}	Peak gate current	$I_{TM} = 20\text{ A}; I_G = 0.2\text{ A};$ $dI_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100			$\text{A}/\mu\text{s}$
V_{GM}	Peak gate voltage		-	2			A
P_{GM}	Peak gate power		-	5			V
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	5			W
T_{stg}	Storage temperature		-40	150			$^\circ\text{C}$
T_j	Operating junction temperature		-	125			$^\circ\text{C}$

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μs .

Three quadrant triacs high commutation

BTA212X series B

ISOLATION LIMITING VALUE & CHARACTERISTIC

$T_{hs} = 25\text{ °C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	$f = 50\text{-}60\text{ Hz}$; sinusoidal waveform; $R.H. \leq 65\%$; clean and dustfree	-		2500	V
C_{isol}	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Thermal resistance junction to heatsink	full or half cycle with heatsink compound	-	-	4.0	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	without heatsink compound in free air	-	55	5.5	K/W

STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current ²	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$				
		T2+ G+	2	18	50	mA
		T2+ G-	2	21	50	mA
		T2- G-	2	34	50	mA
I_L	Latching current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$				
		T2+ G+	-	31	60	mA
		T2+ G-	-	34	90	mA
		T2- G-	-	30	60	mA
I_H	Holding current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$	-	31	60	mA
V_T	On-state voltage	$I_T = 17\text{ A}$	-	1.3	1.6	V
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$	0.25	0.4	-	V
I_D	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}$; $T_j = 125\text{ °C}$; exponential waveform; gate open circuit	1000	4000	-	V/ μ s
dI_{com}/dt	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}$; $T_j = 125\text{ °C}$; $I_{T(RMS)} = 12\text{ A}$; without snubber; gate open circuit	-	24	-	A/ms
t_{gt}	Gate controlled turn-on time	$I_{TM} = 12\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu$ s	-	2	-	μ s

² Device does not trigger in the T2-, G+ quadrant.

Three quadrant triacs
high commutation

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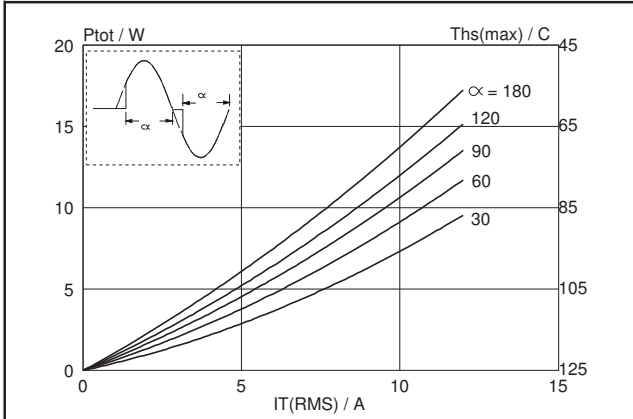


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha =$ conduction angle.

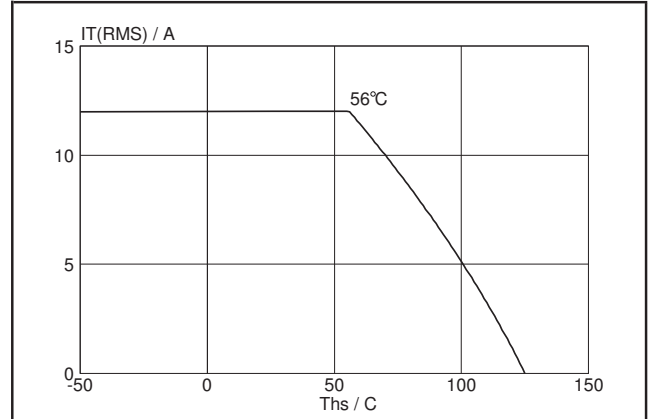


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus heatsink temperature T_{hs} .

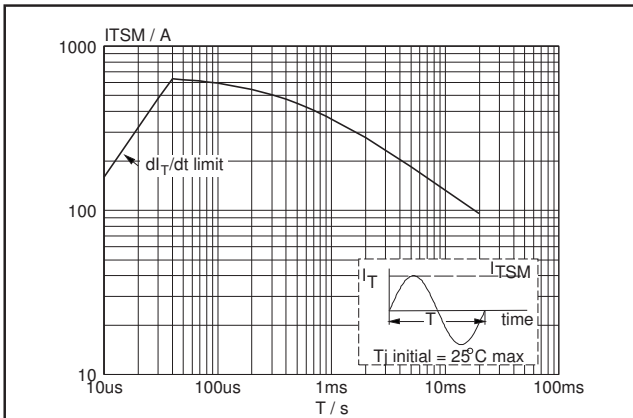


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 20$ ms.

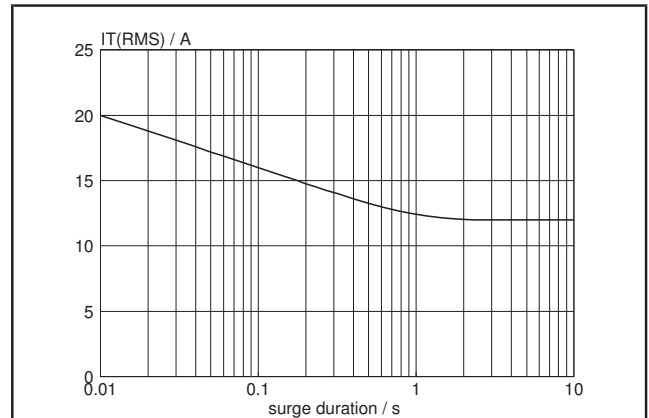


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50$ Hz; $T_{hs} \leq 56$ °C.

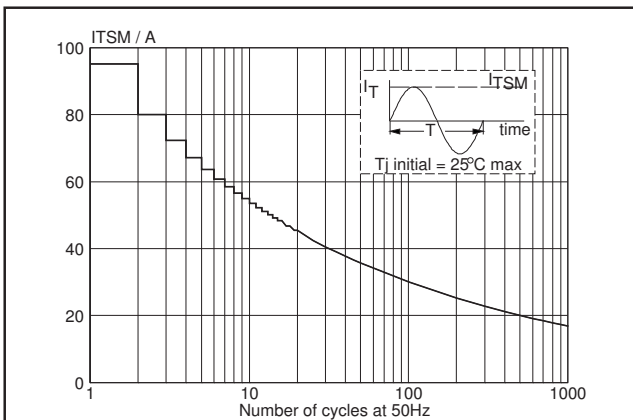


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50$ Hz.

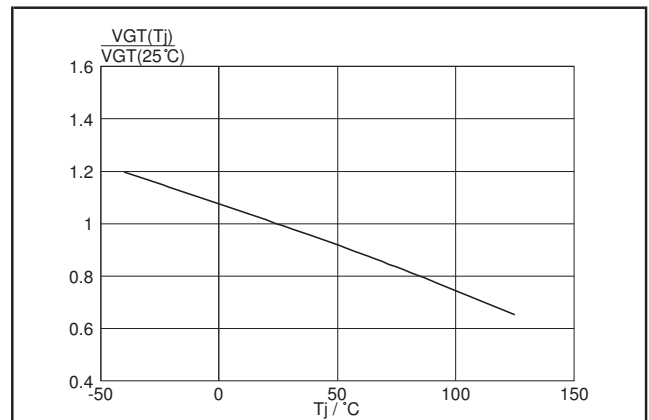
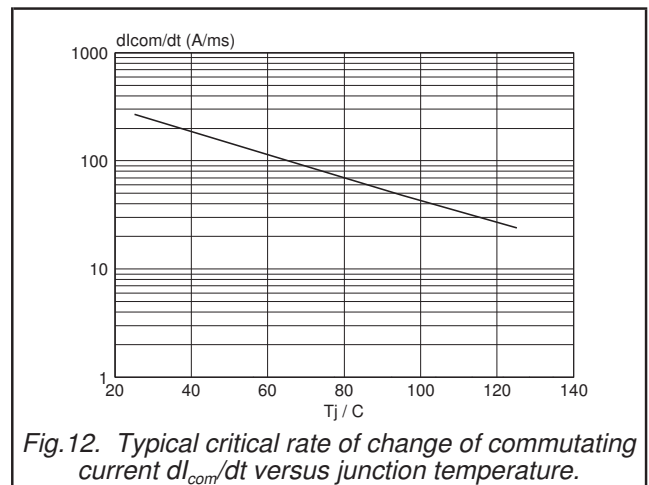
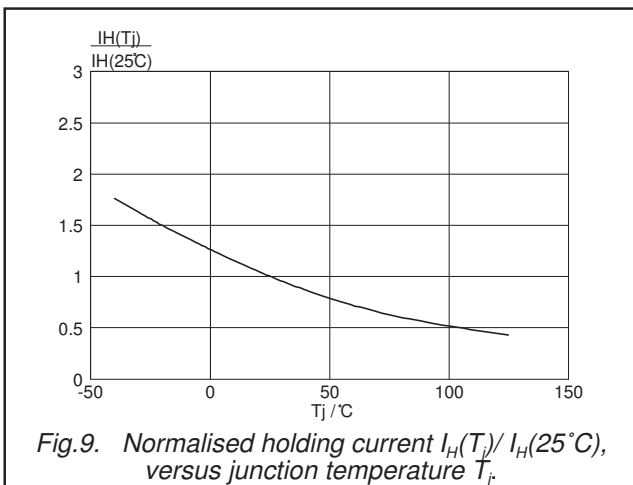
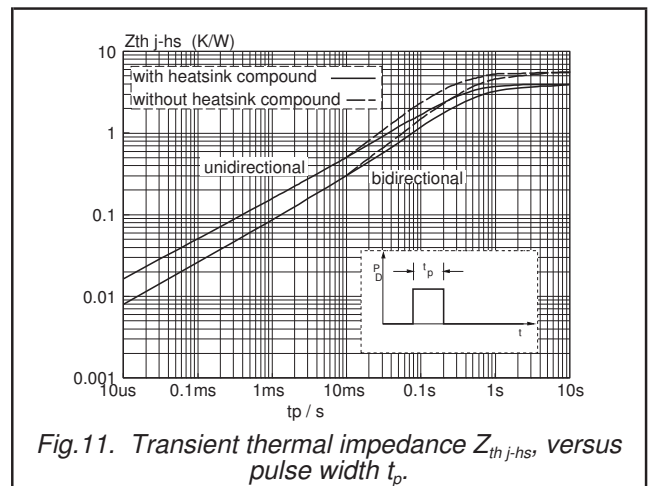
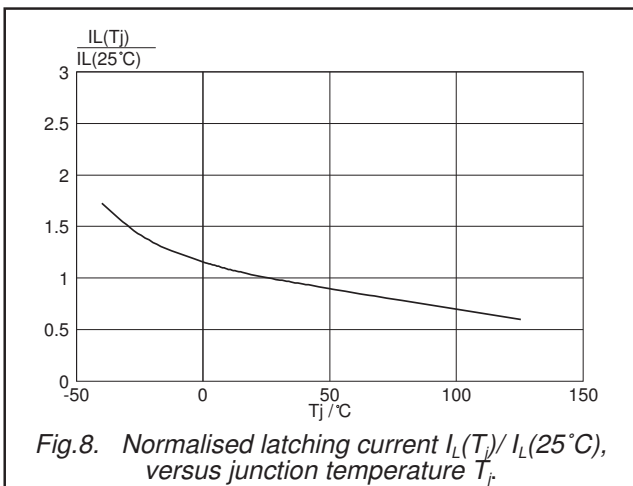
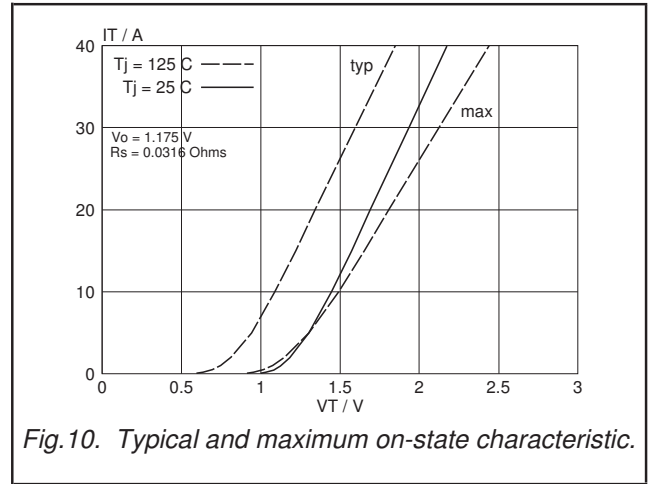
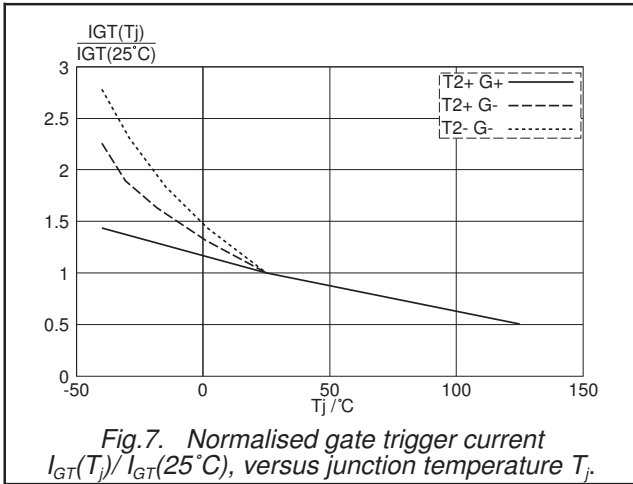


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j) / V_{GT}(25^\circ C)$, versus junction temperature T_j .

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high commutation

BTA212X series B

MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

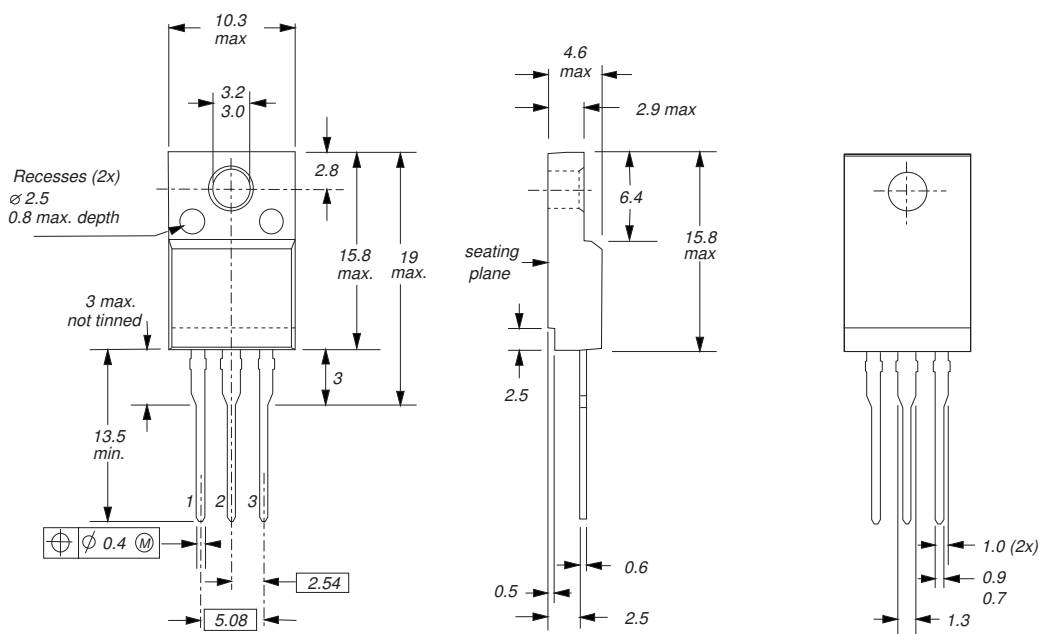


Fig. 13. SOT186A; The seating plane is electrically isolated from all terminals.

Notes

1. Refer to mounting instructions for F-pack envelopes.
2. Epoxy meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Contact information

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